

Listing of claims:

1. **(Currently amended)** Composition A composition for the production of semiconductors, comprising H_2SiF_6 and/or HBF_4 in a total amount of 10-500 mg/kg, 12-17% by weight of H_2SO_4 , 2-4% by weight of H_2O_2 , optionally in combination with additives, in aqueous solution.

2. **(Currently amended)** Use of a A process for residual polymer removal from a semiconductor surface comprising contacting a semiconductor surface with a composition comprising H_2SiF_6 and/or HBF_4 as residual polymer remover in a process step in the production of semiconductors with the structured semiconductor surface in order to remove residual polymers from the structured semiconductor surface.

3. **(Currently amended)** A process Use according to claim 2 for the removal of residual polymers from Al or Al-containing conductor tracks on said semiconductor surface.

4. **(Currently amended)** Use A process according to claim 2 for the removal of residual polymers after dry etching on metal conductor tracks and contact holes on said semiconductor surface.

5. **(Currently amended)** A process for the removal of residual polymers from aluminium or copper/aluminium alloys Use of a comprising contacting a semiconductor surface having aluminium or copper/aluminium alloys with a composition according to claim 1 for the removal of residual polymers from aluminium or copper/aluminium alloys.

6. **(Currently amended)** Use of a A process for residual polymer removal from a semiconductor surface comprising contacting a semiconductor surface with a

composition comprising H_2SiF_6 and/or HBF_4 in a total amount of 10-500 mg/kg, 12-17% by weight of H_2SO_4 , 2-4% by weight of H_2O_2 , optionally in combination with additives, in aqueous solution, ~~according to claim 2.~~

7. **(Currently amended)** ~~Use~~ A process according to claim 2 ~~for the removal of residual polymers in a process step in the production of semiconductors using further comprising contacting a semiconductor surface with a composition~~ comprising H_2SiF_6 and/or HBF_4 in a spin etcher or in a tank unit.

8. **(Currently amended)** ~~Process~~ A process for the removal of residual polymers from Al or Al-containing conductor tracks, ~~characterised in that wherein residual~~ polymers are removed using a composition according to claim 1.

9. **(New)** A composition according to claim 1, comprising 12% by weight of H_2SO_4 , 2.4% by weight of H_2O_2 , 100 ppm of H_2SiF_6 and a surfactant.

10. **(New)** A composition according to claim 1, comprising 600 ppm H_2SiF_6 .

11. **(New)** A process according to claim 6, for the removal of residual polymers after dry etching on metal conductor tracks and contact holes on said semiconductor surface.